

FIG. 1 (prior art)

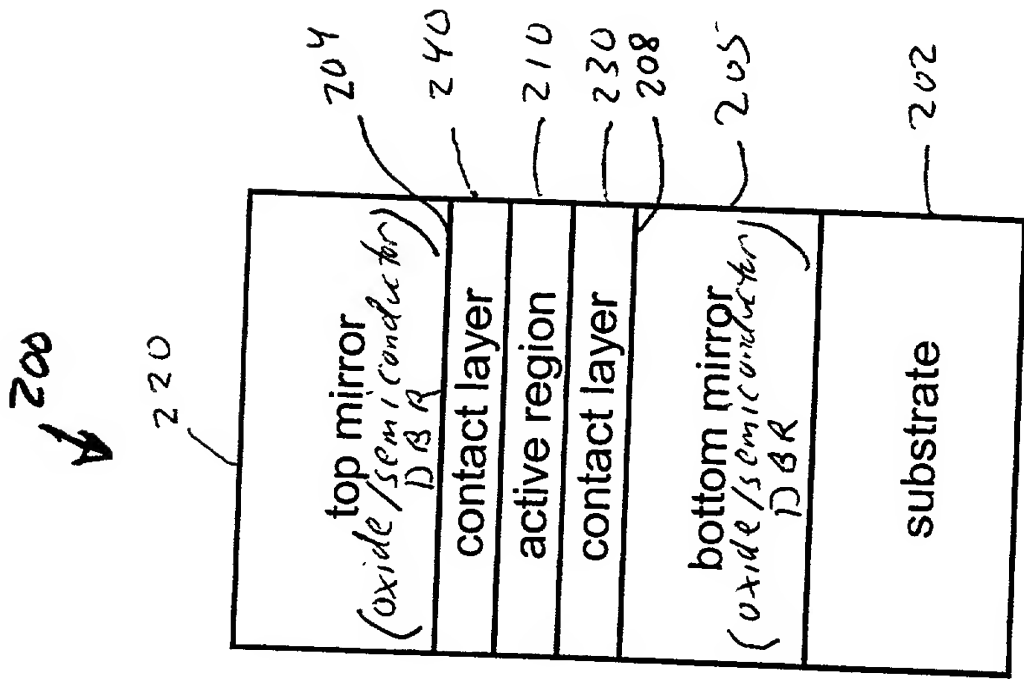


FIG. 2A

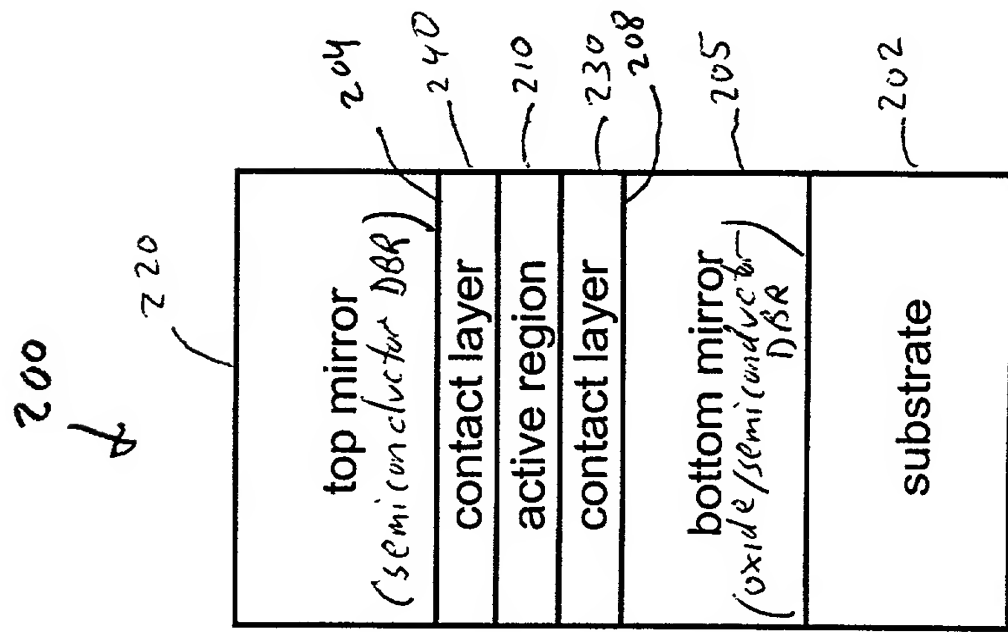


FIG. 2B

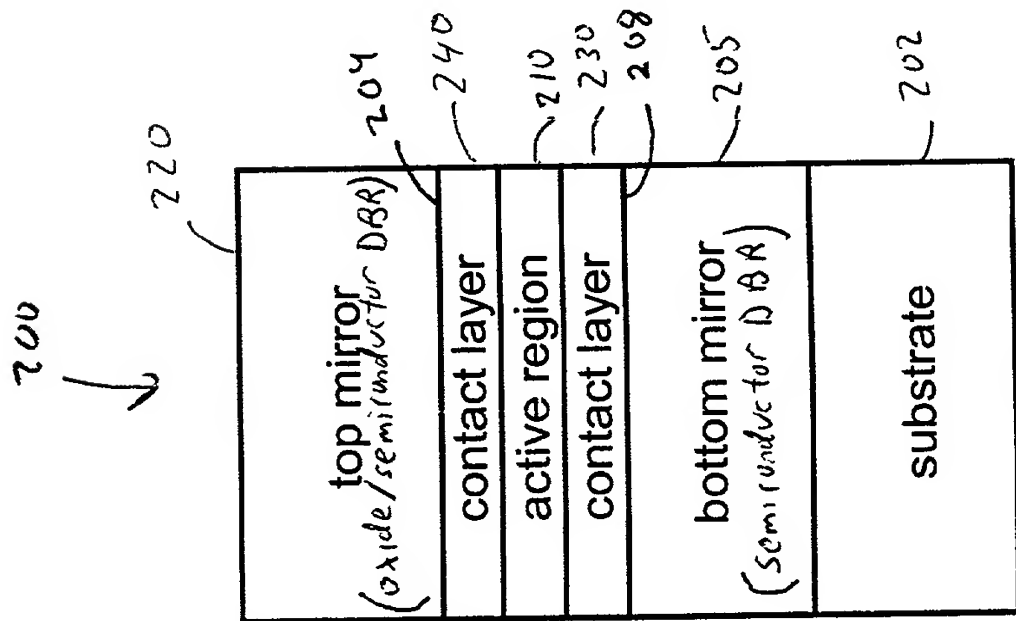


FIG. 2C

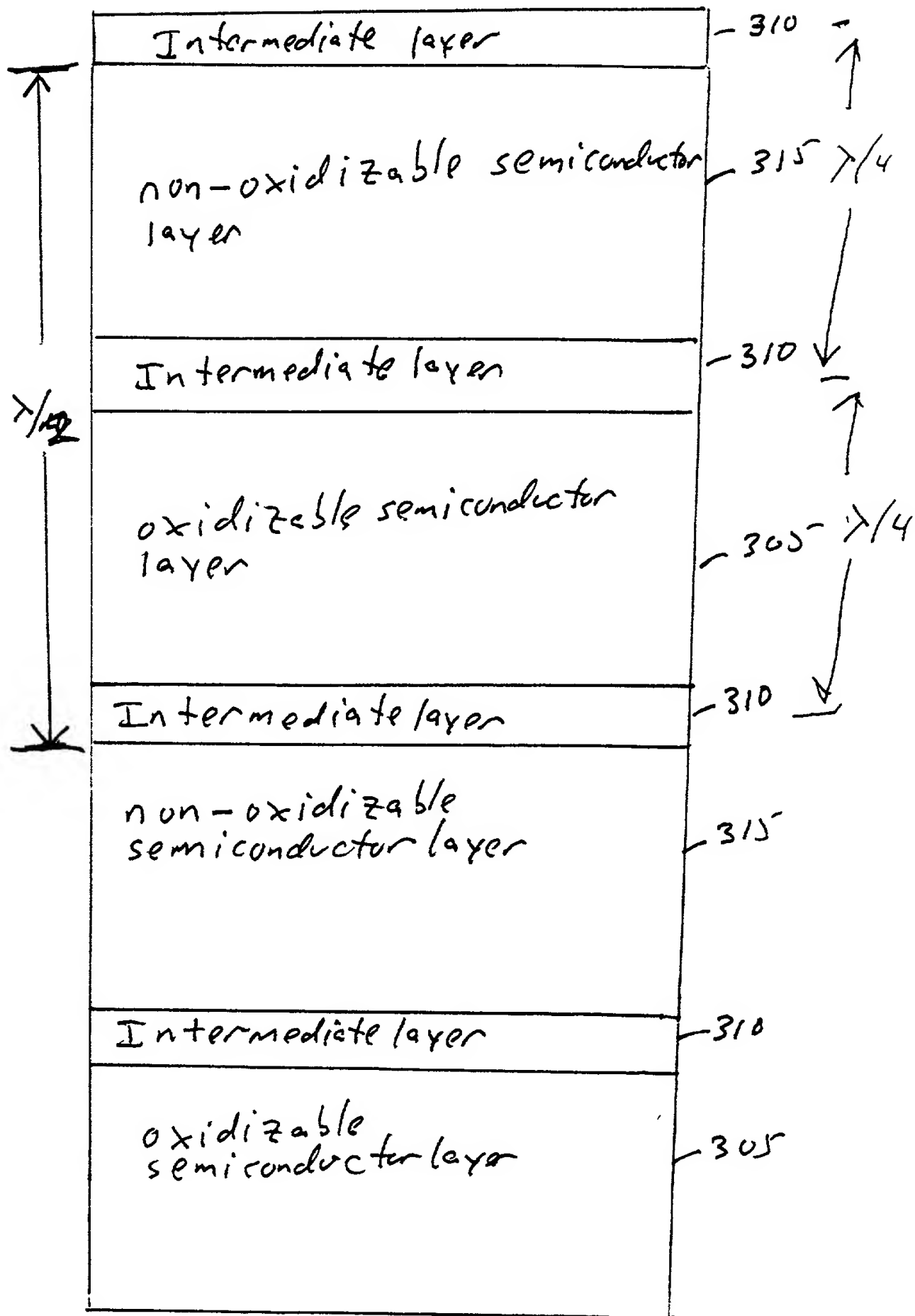


FIG. 3

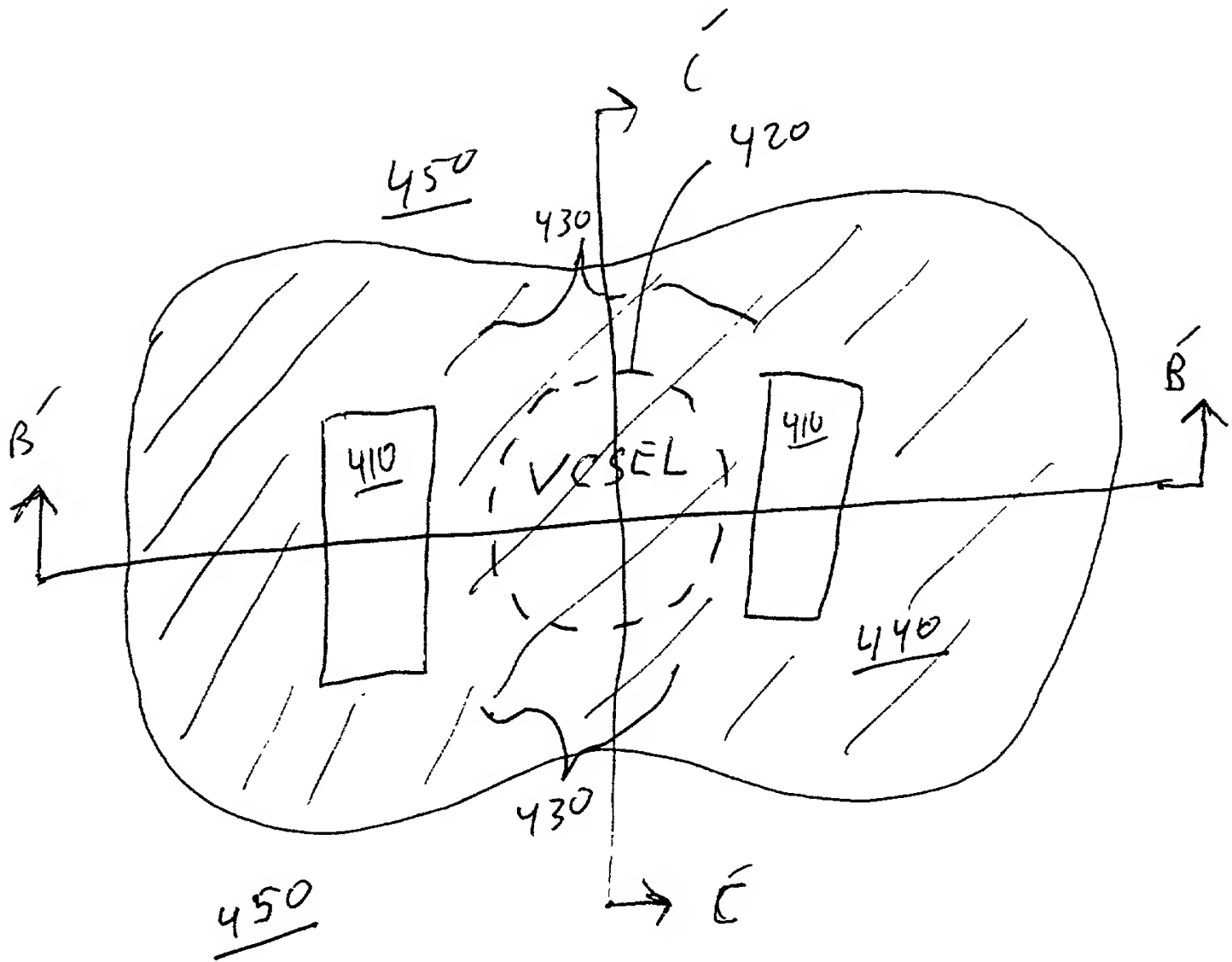


FIG. 4A

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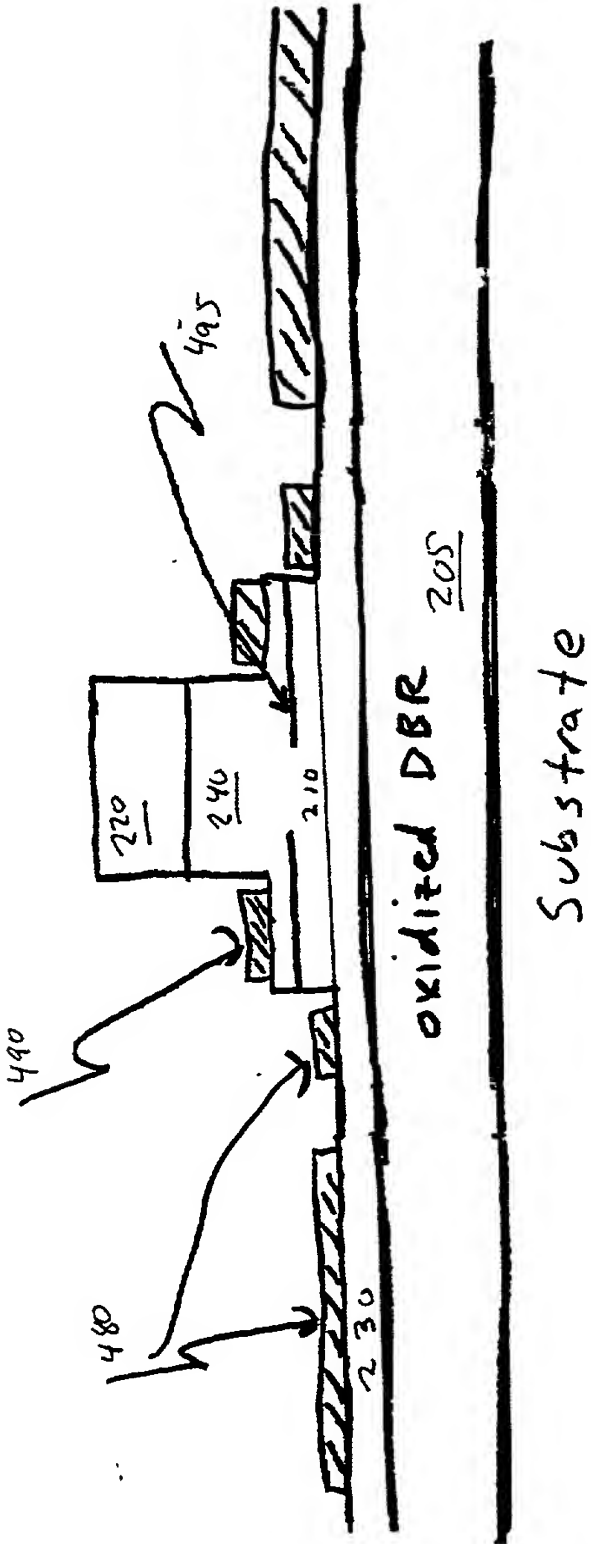


FIG. 4C

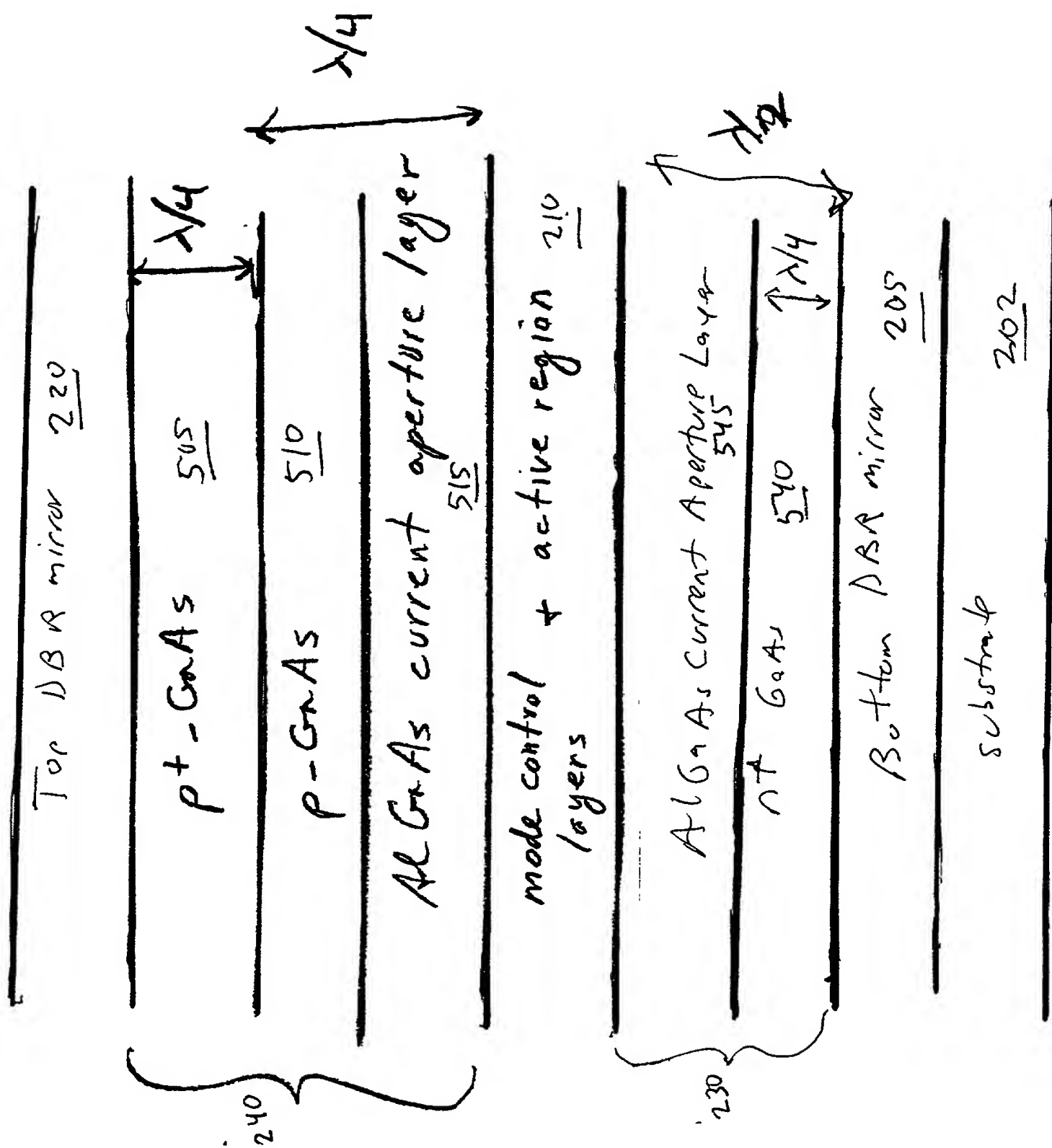
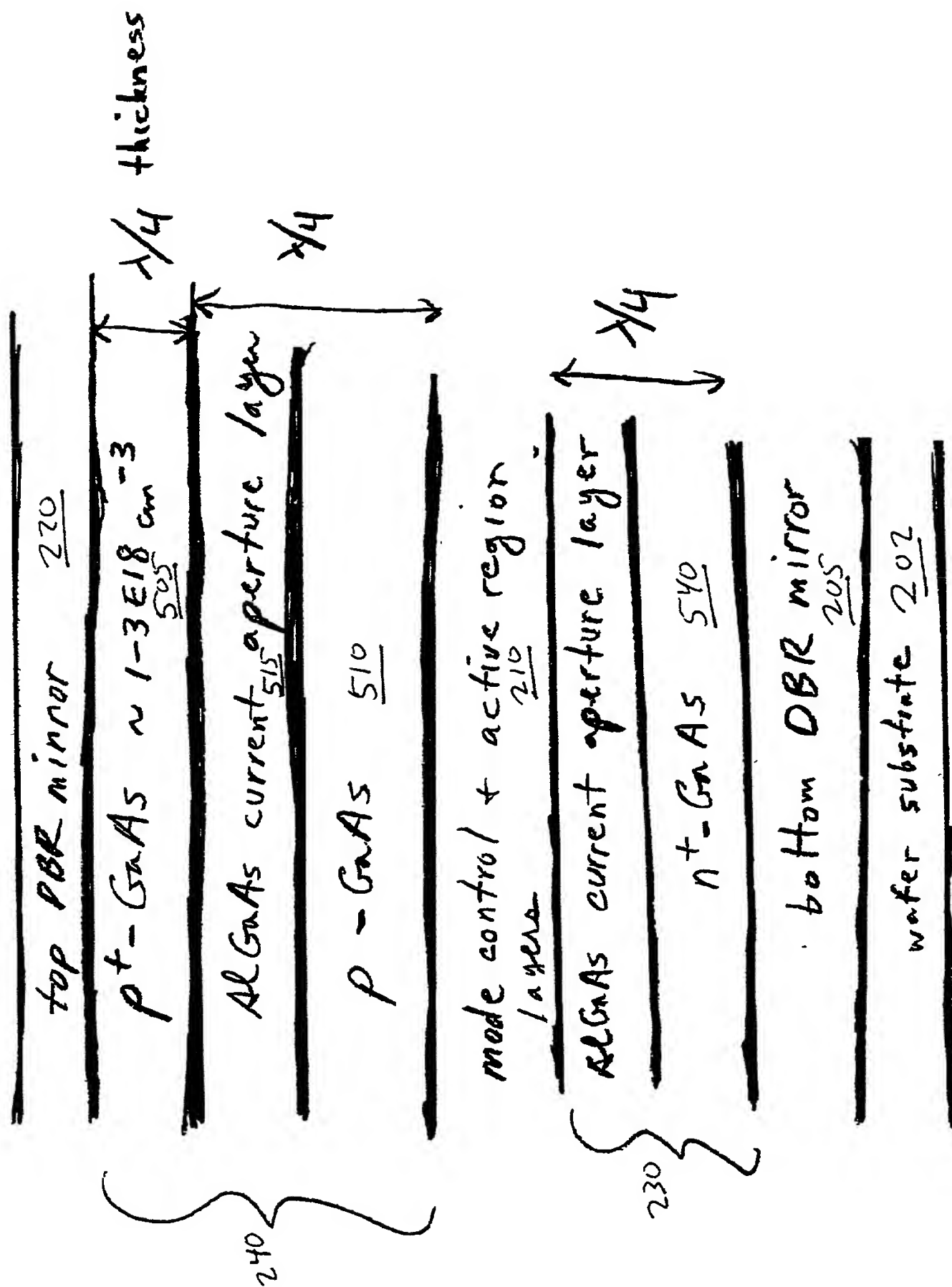


FIG. 5A



ETG. SB

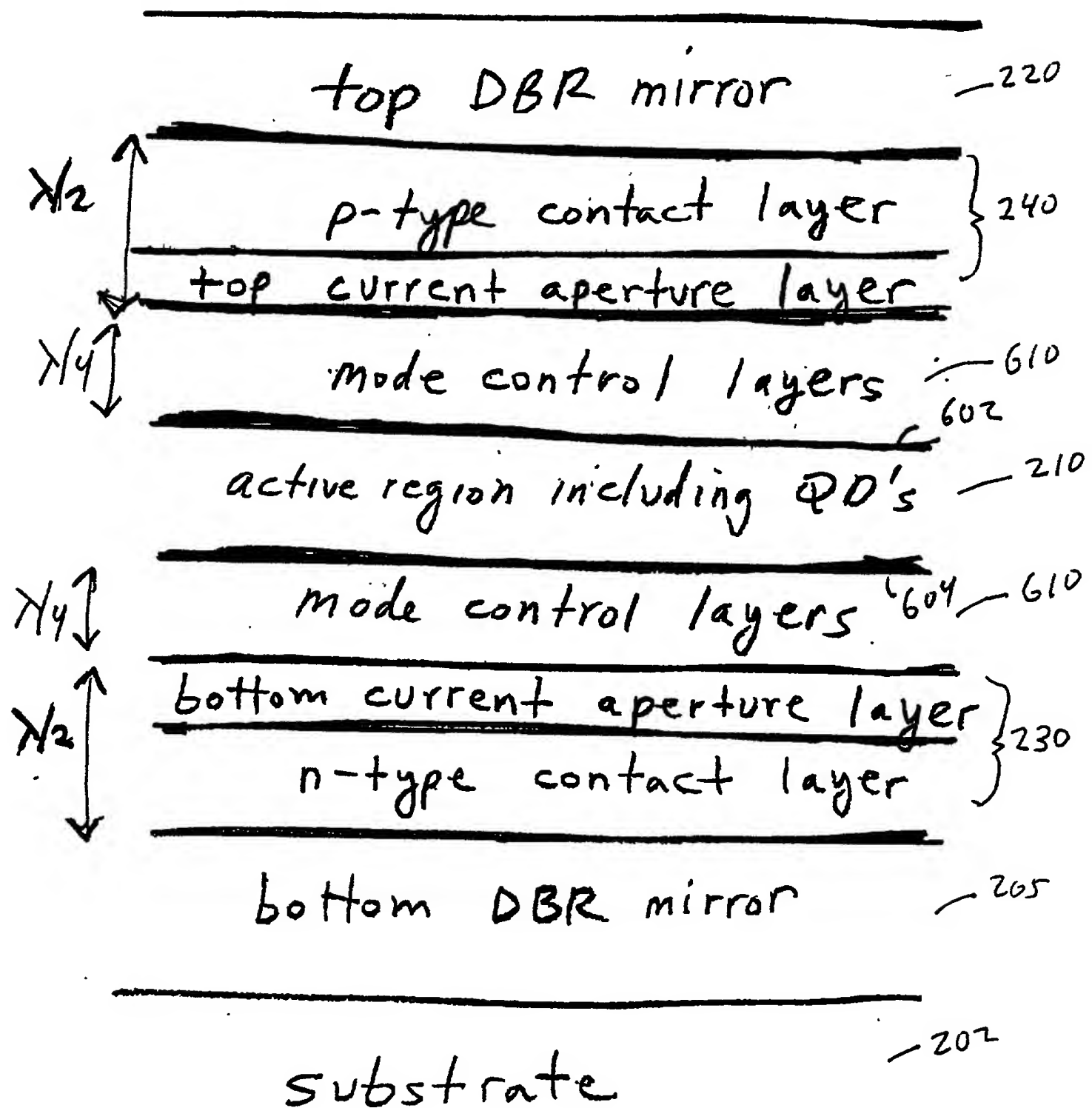


FIG. 6A

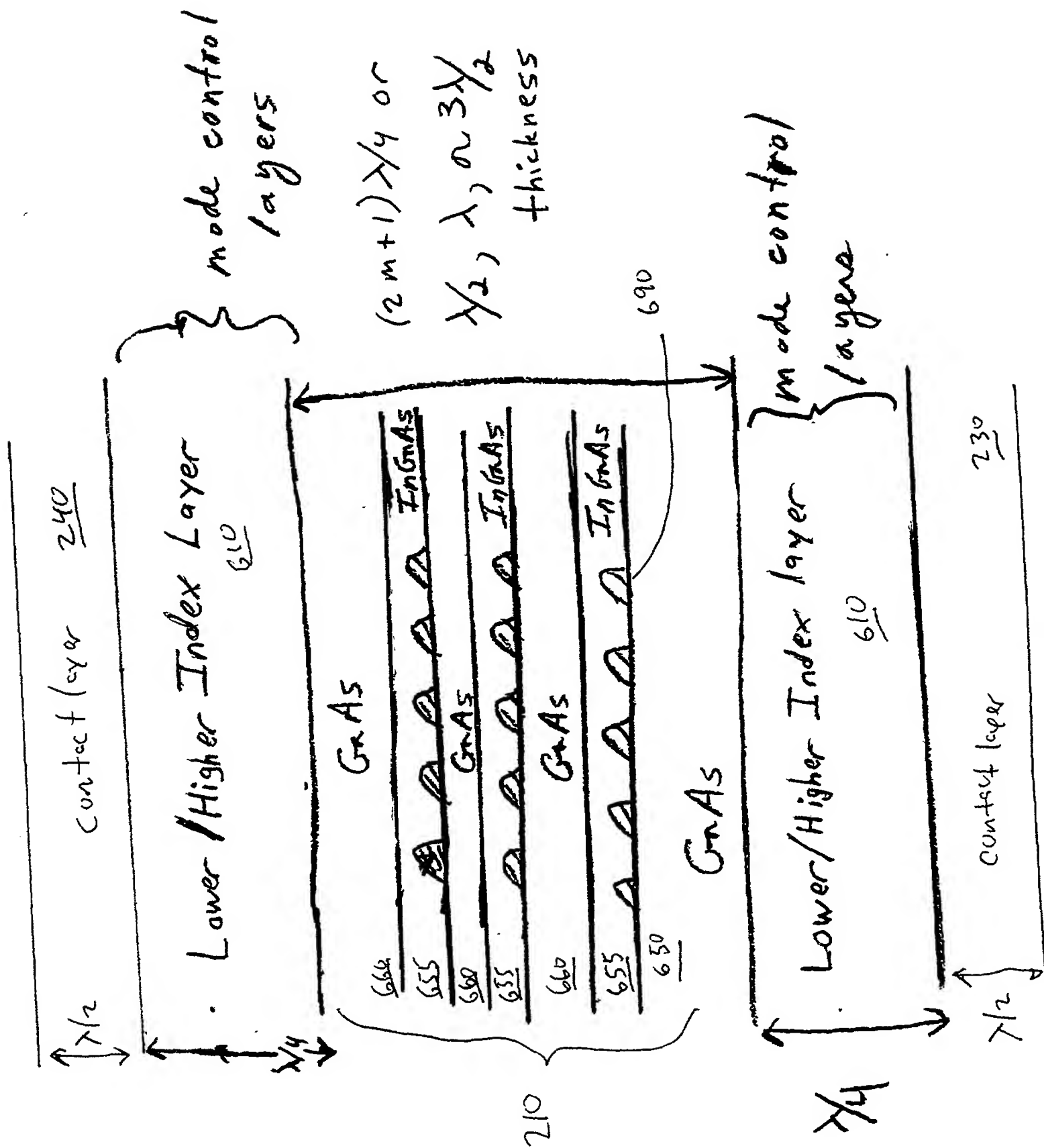


FIG. 6B

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↓

120	GaAs	92nm, 5x
	Al _{0.92} Ga _{0.08} As	10nm, 5x
	AlAs	213nm, 5x
	Al _{0.92} Ga _{0.08} As	10nm, 5x
	GaAs, p ³¹⁸	92nm p-contact
240	Al _{0.92} Ga _{0.08} As, p ¹⁷	107nm Mode Control
610	GaAs, p ¹⁷	71nm p-contact
	Al _{0.98} Ga _{0.02} As, p ¹⁶	50nm Current aperture
	Al _{0.92} Ga _{0.08} As	12nm grade for current aperture
	GaAs	20nm Active
	GaAs	10nm, 3x 600C Active
	GaAs	0.8nm, 3x Active
	In _{0.15} Ga _{0.85} As	~8nm, 3x Active
210	InAs	2.4ML, 3x Active
	In _{0.15} Ga _{0.85} As	1nm, 3x 510C Active
	GaAs	159nm Active
610	Al _{0.92} Ga _{0.08} As, n ¹⁷	107nm Mode Control
230	GaAs, n ²¹⁸	92nm n-contact
	Al _{0.92} Ga _{0.08} As	10nm, 8x
	AlAs	213nm, 8x
205	Al _{0.92} Ga _{0.08} As	10nm, 8x
	GaAs	92nm, 8x
	Al _{0.92} Ga _{0.08} As	10nm
	AlAs	213nm
	Al _{0.92} Ga _{0.08} As	10nm
	GaAs	200nm 600C
	GaAs N+ 2" 1-side	Tox=620C, 10min

FIG. 7

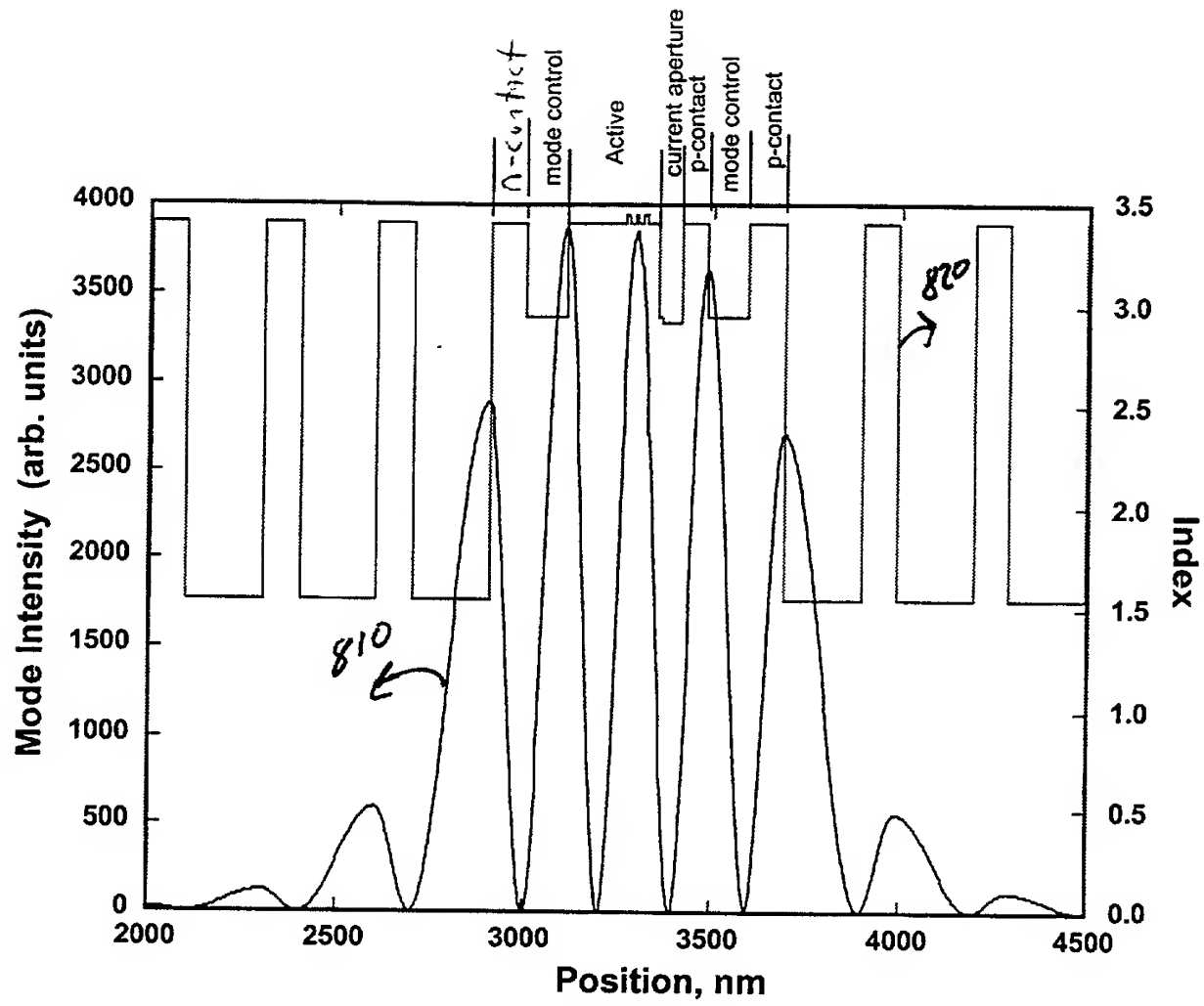


FIG. 8

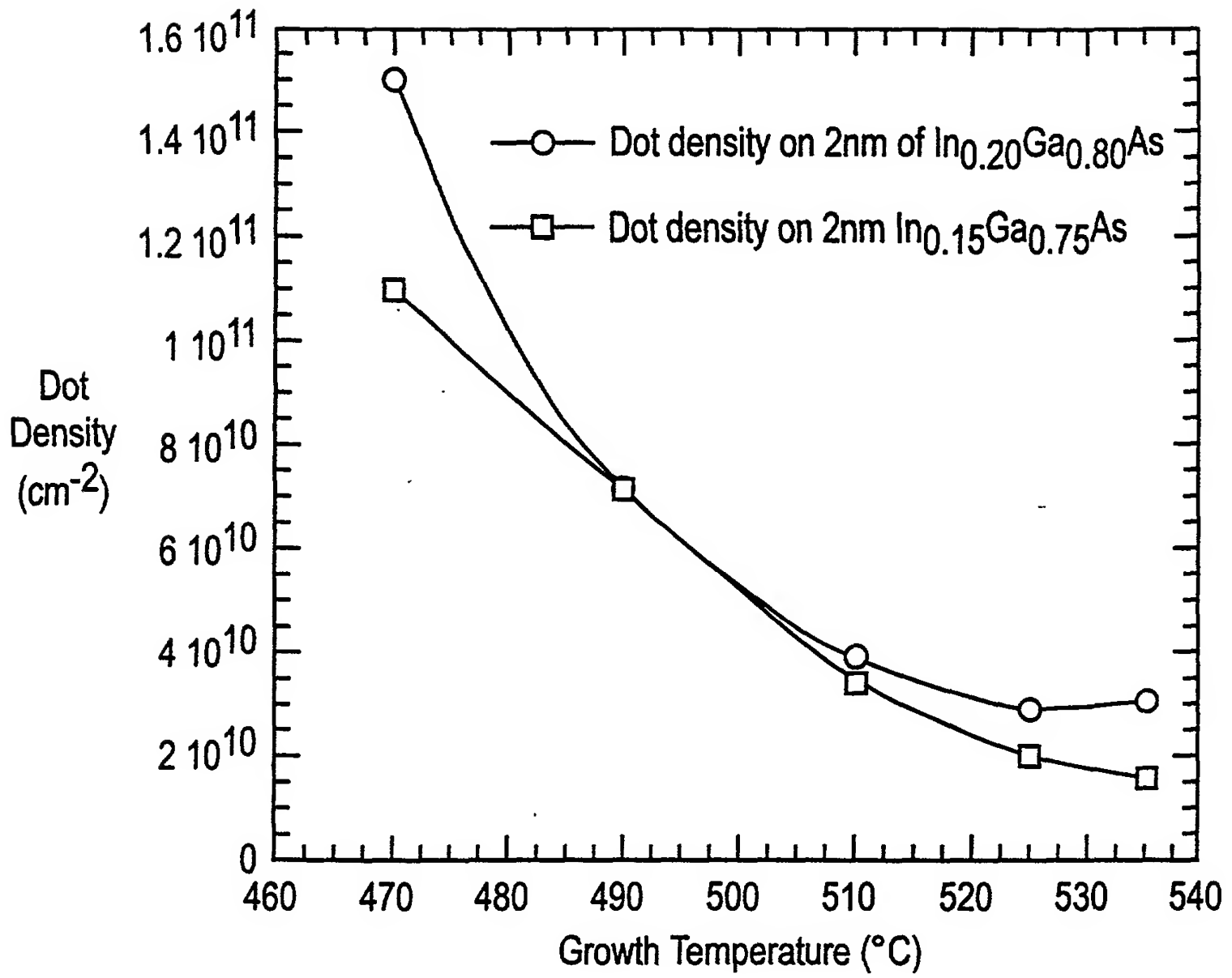


FIG. 9

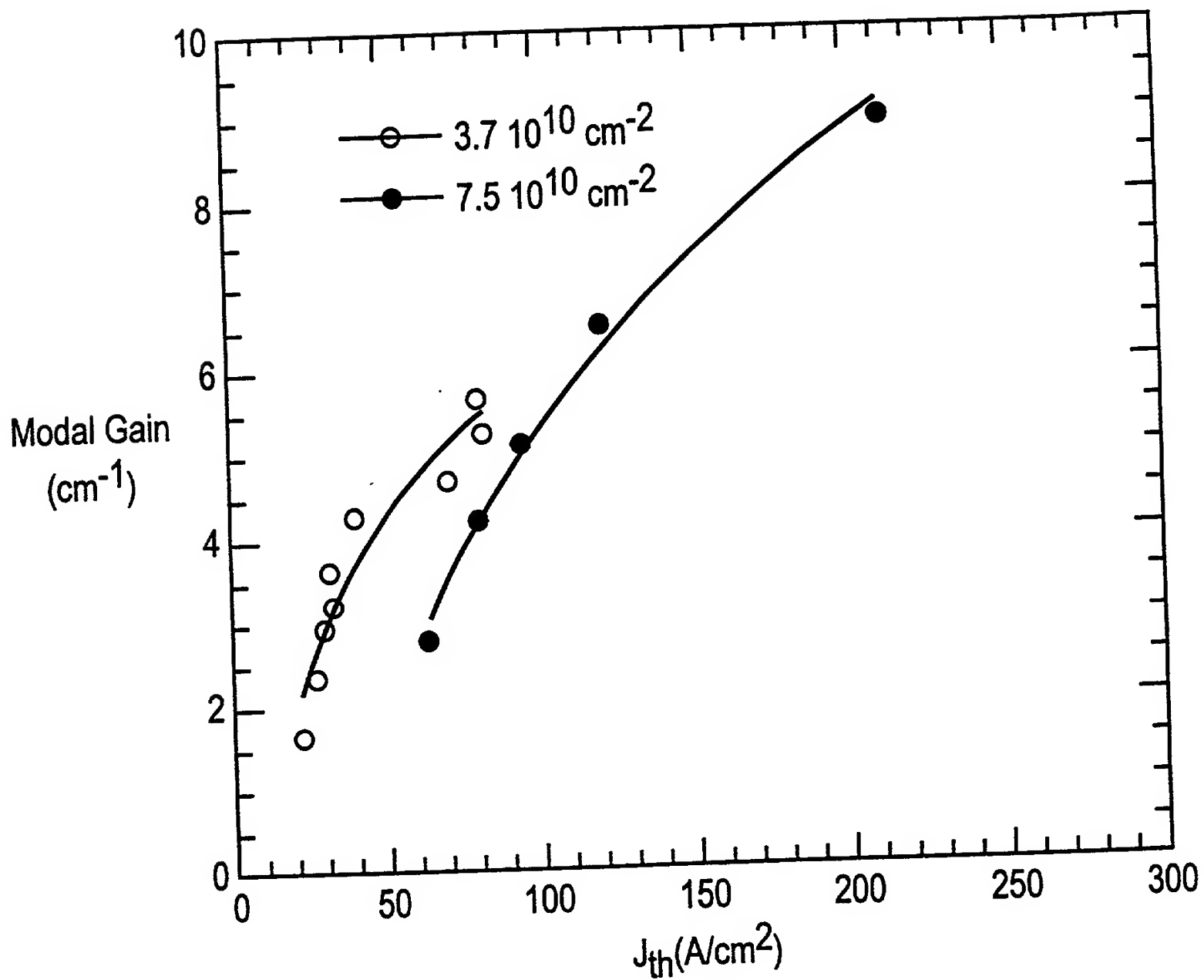


FIG. 10

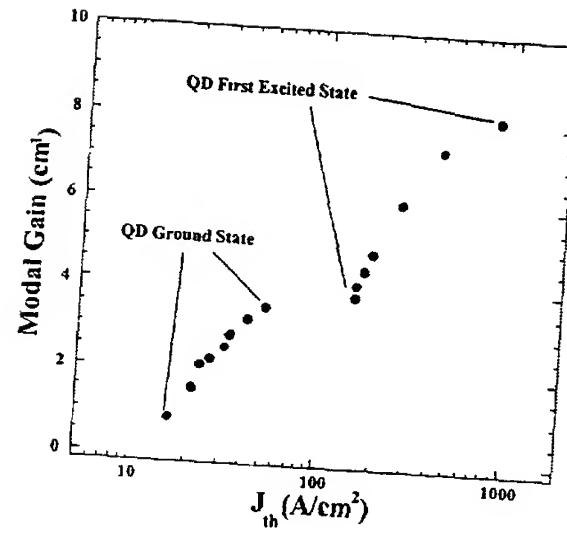


FIG. 11

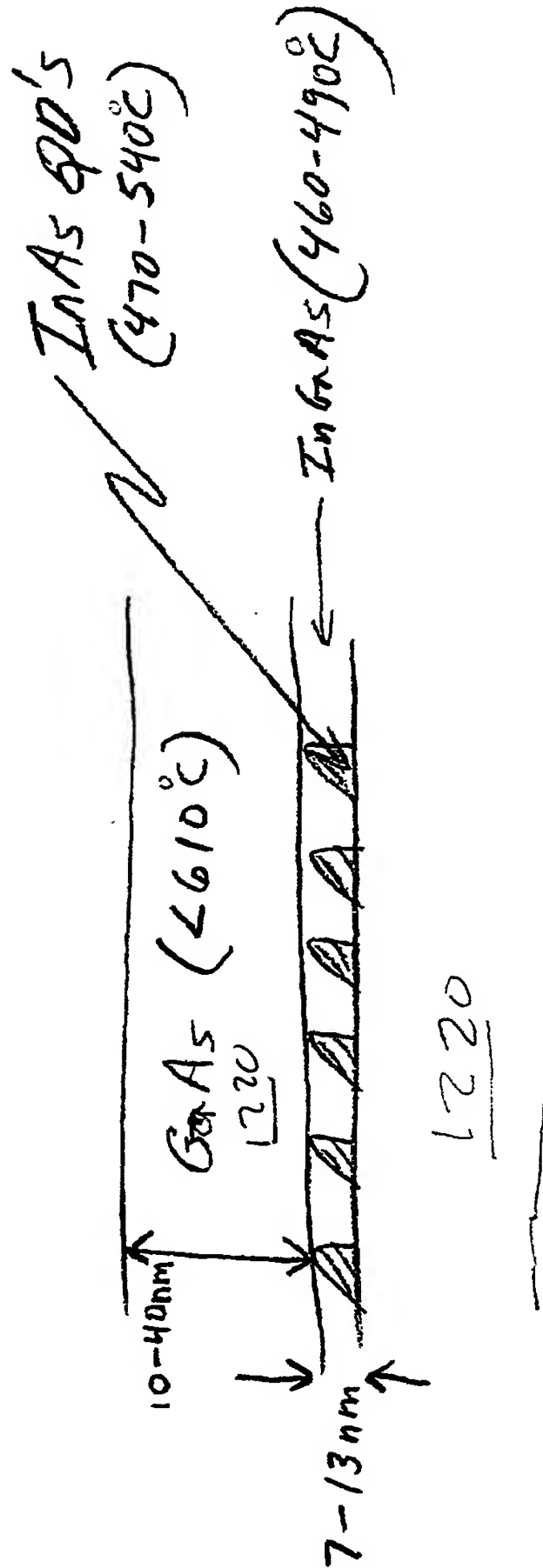


FIG. 12A

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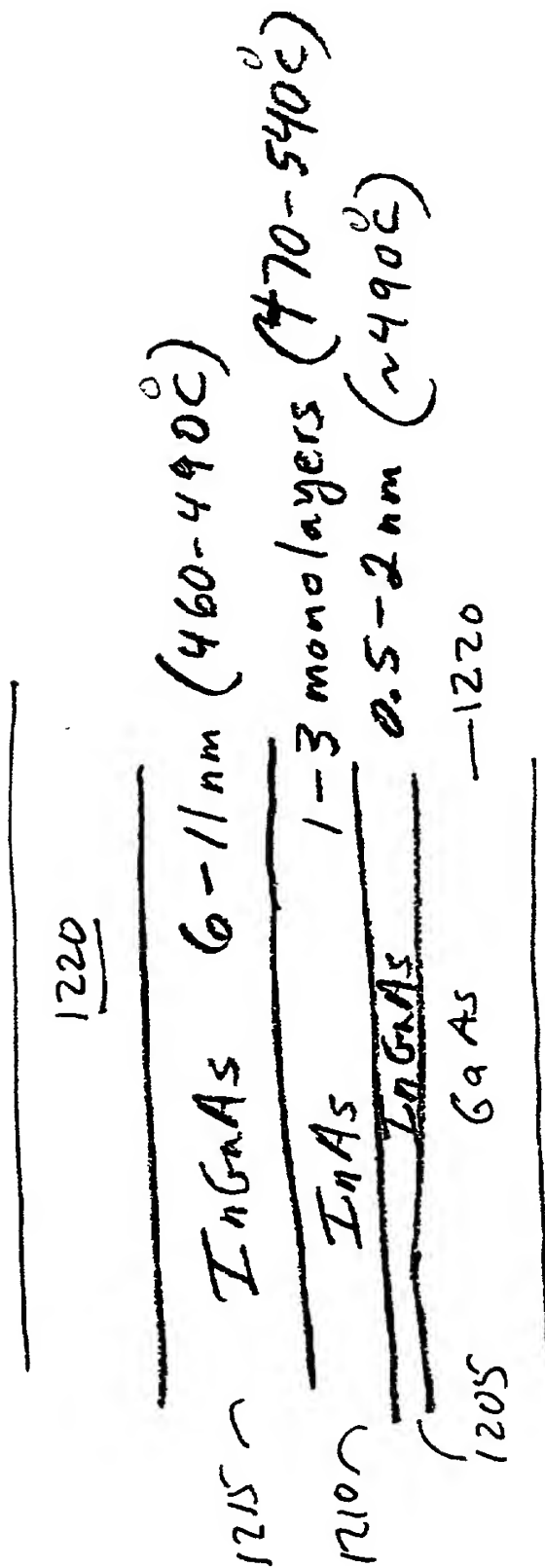


FIG. 12B

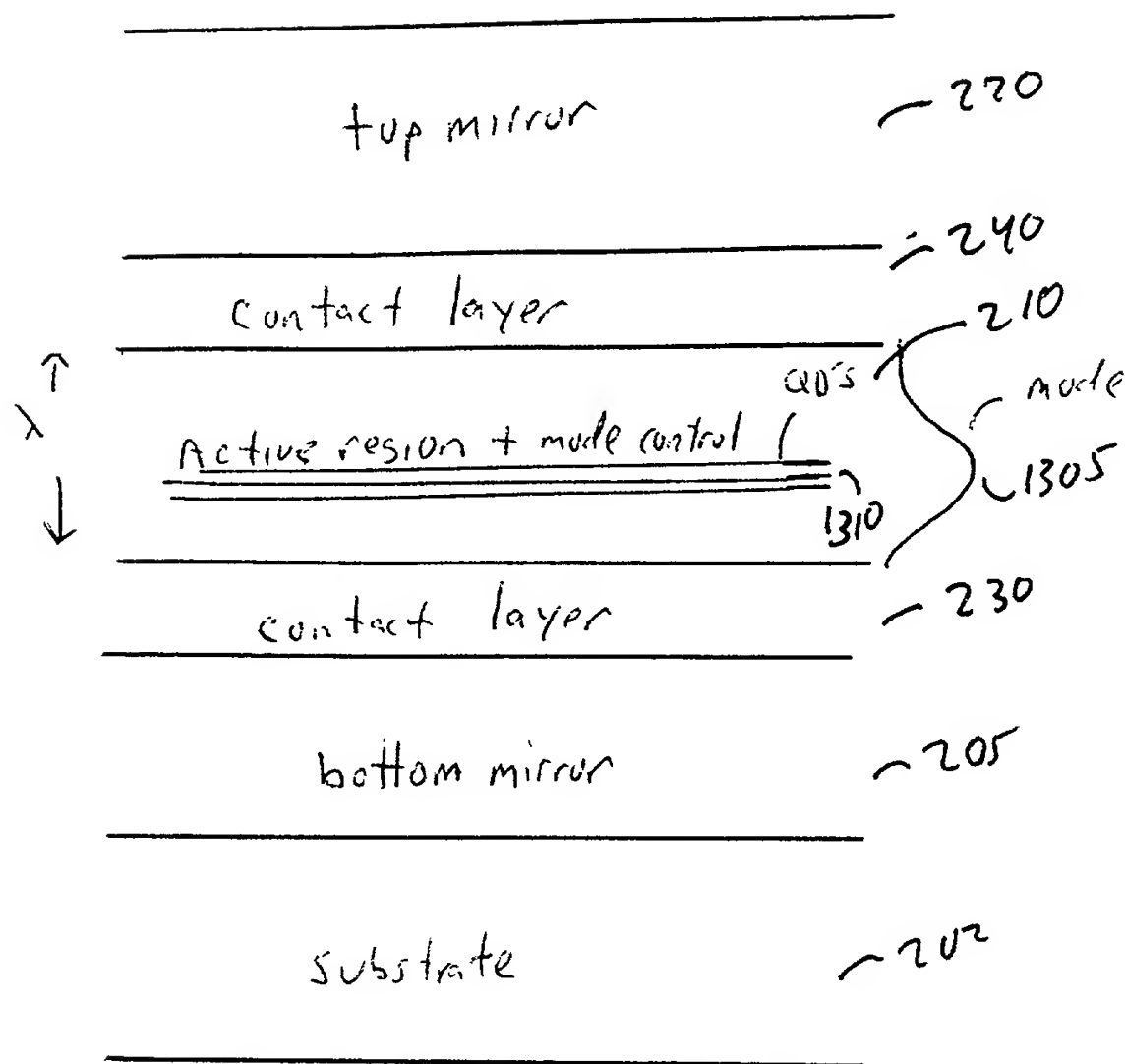


FIG. 13

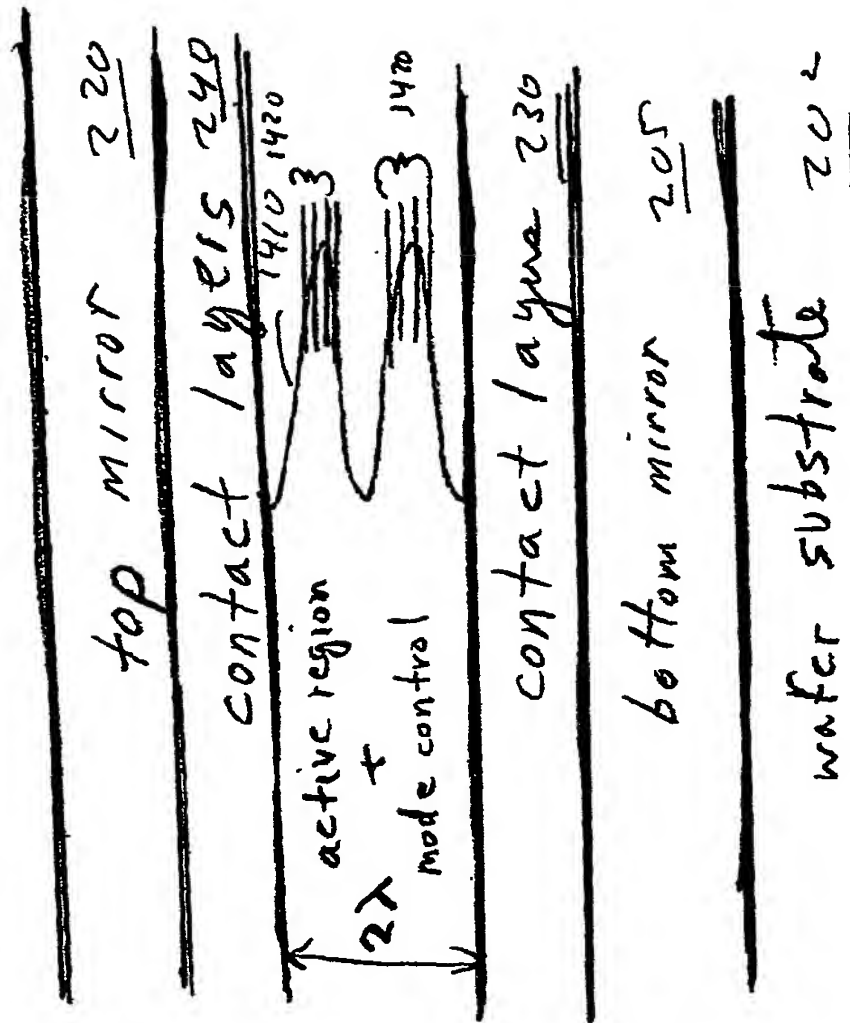


FIG. 14

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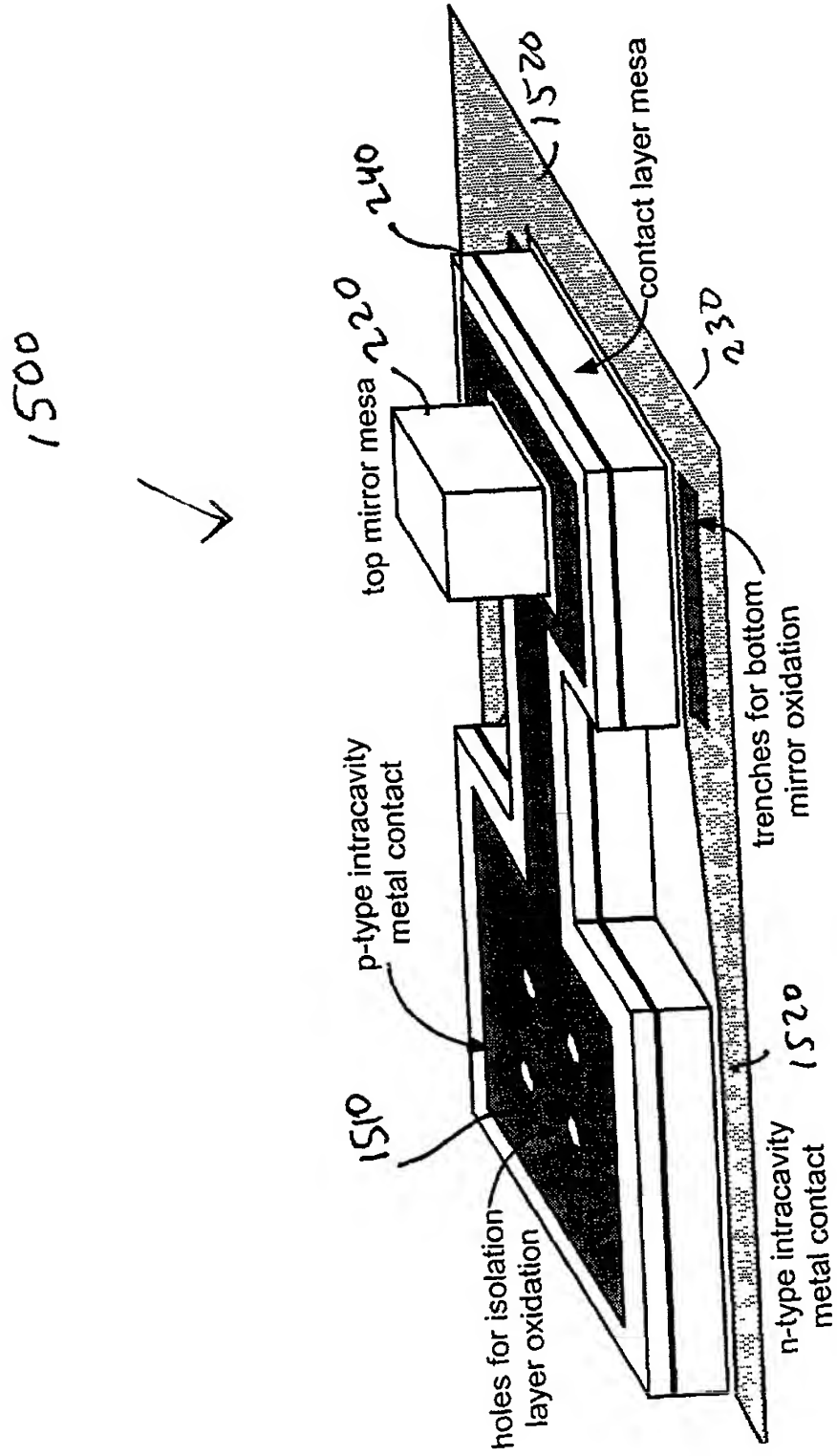


FIG. 15A

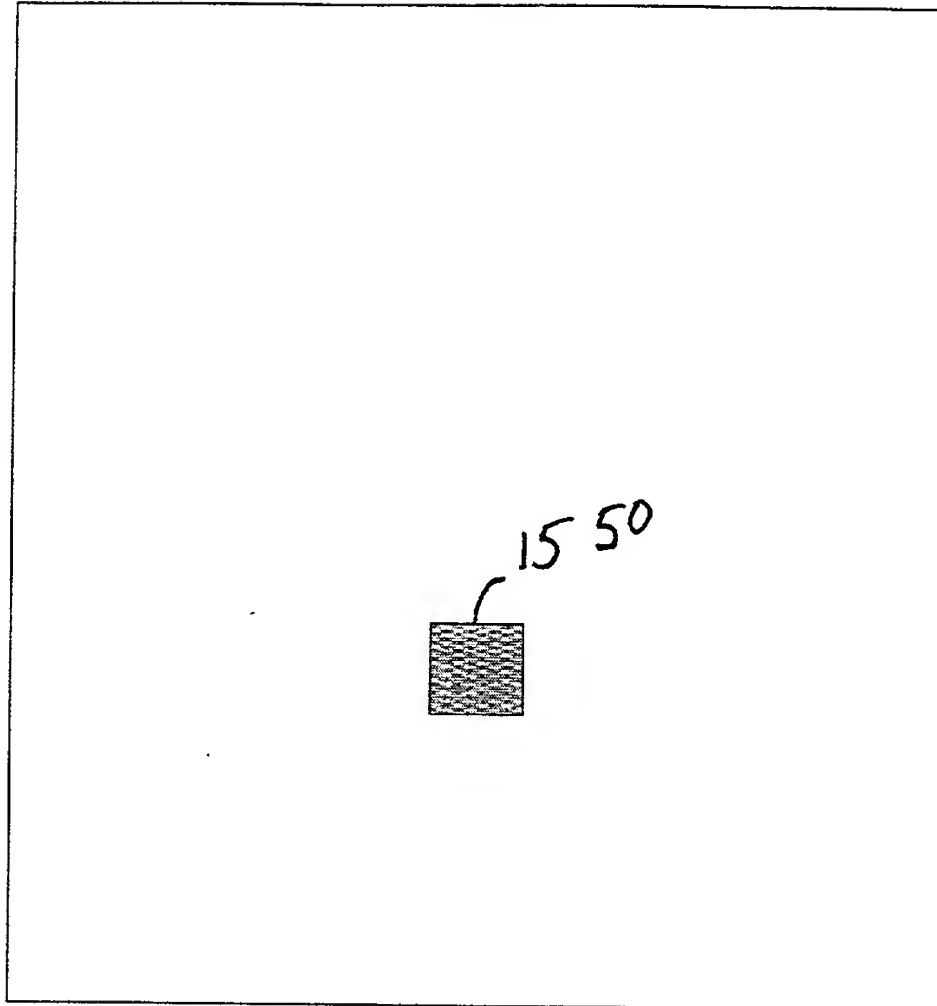


FIG. 15B

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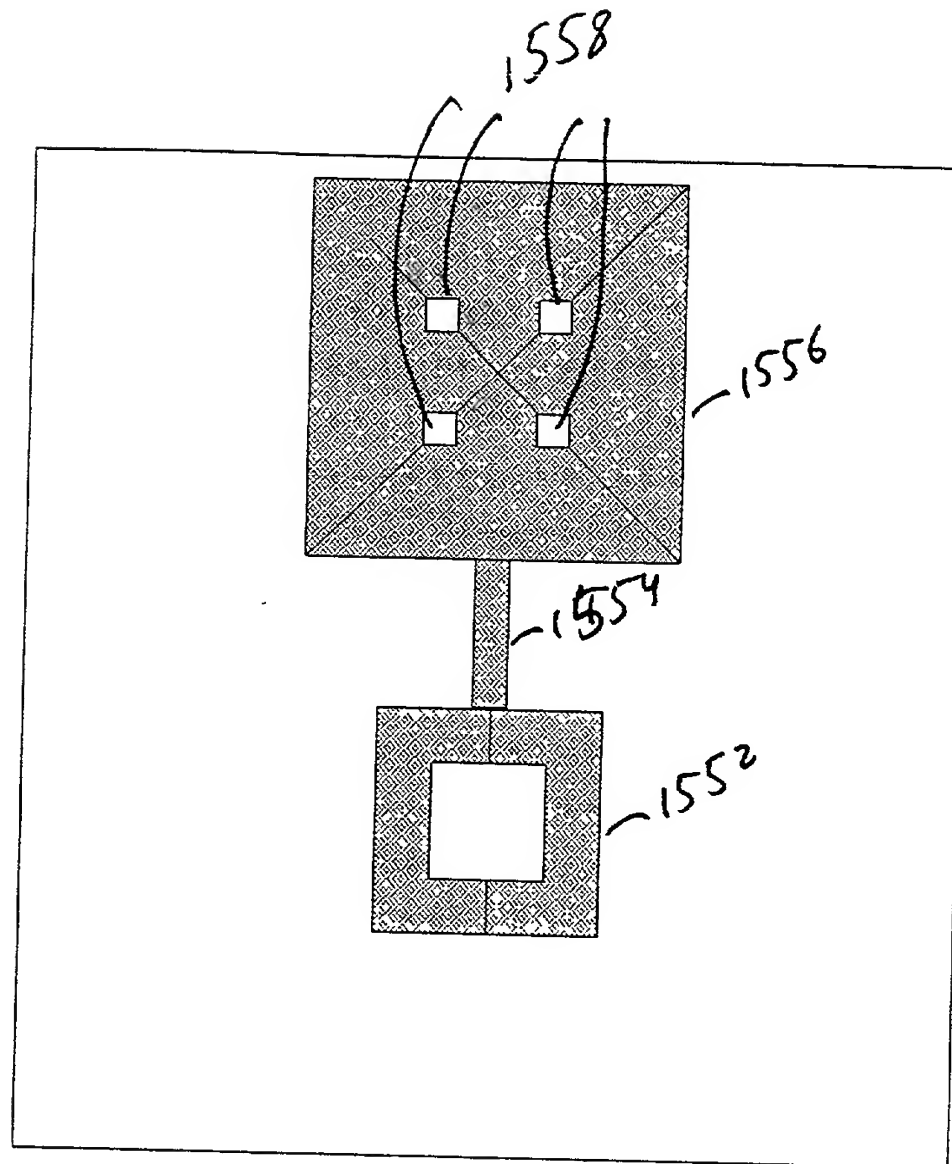


FIG. 15C

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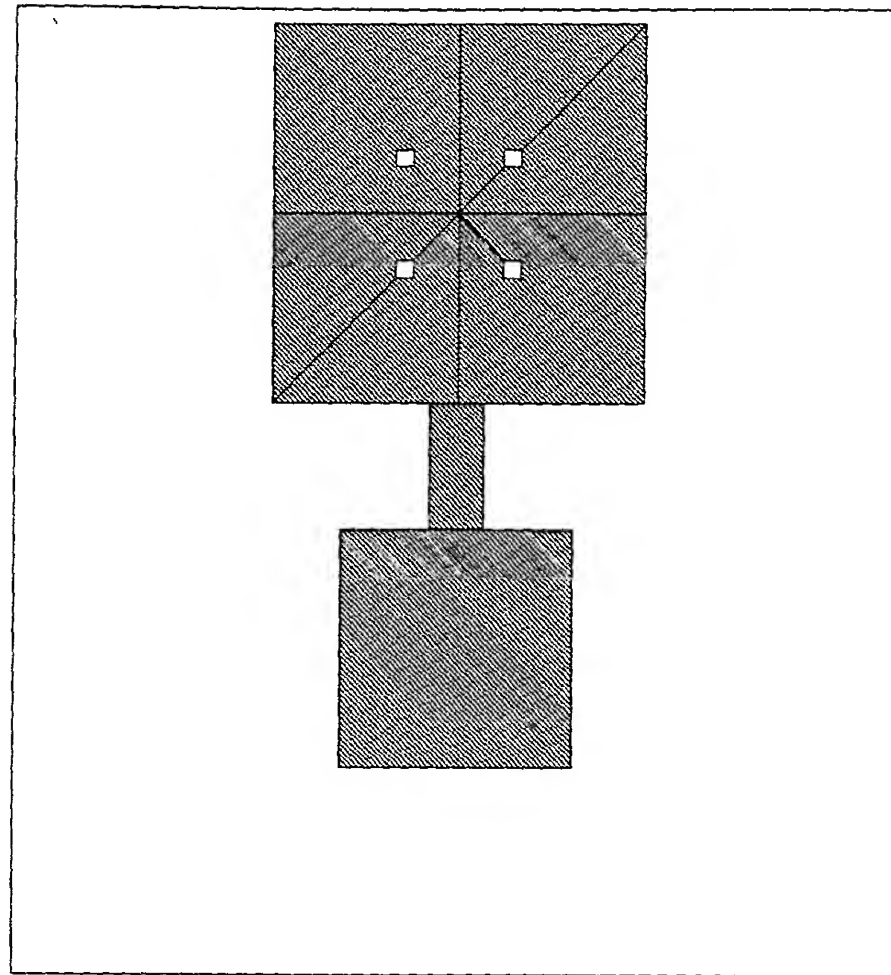


FIG. 15D

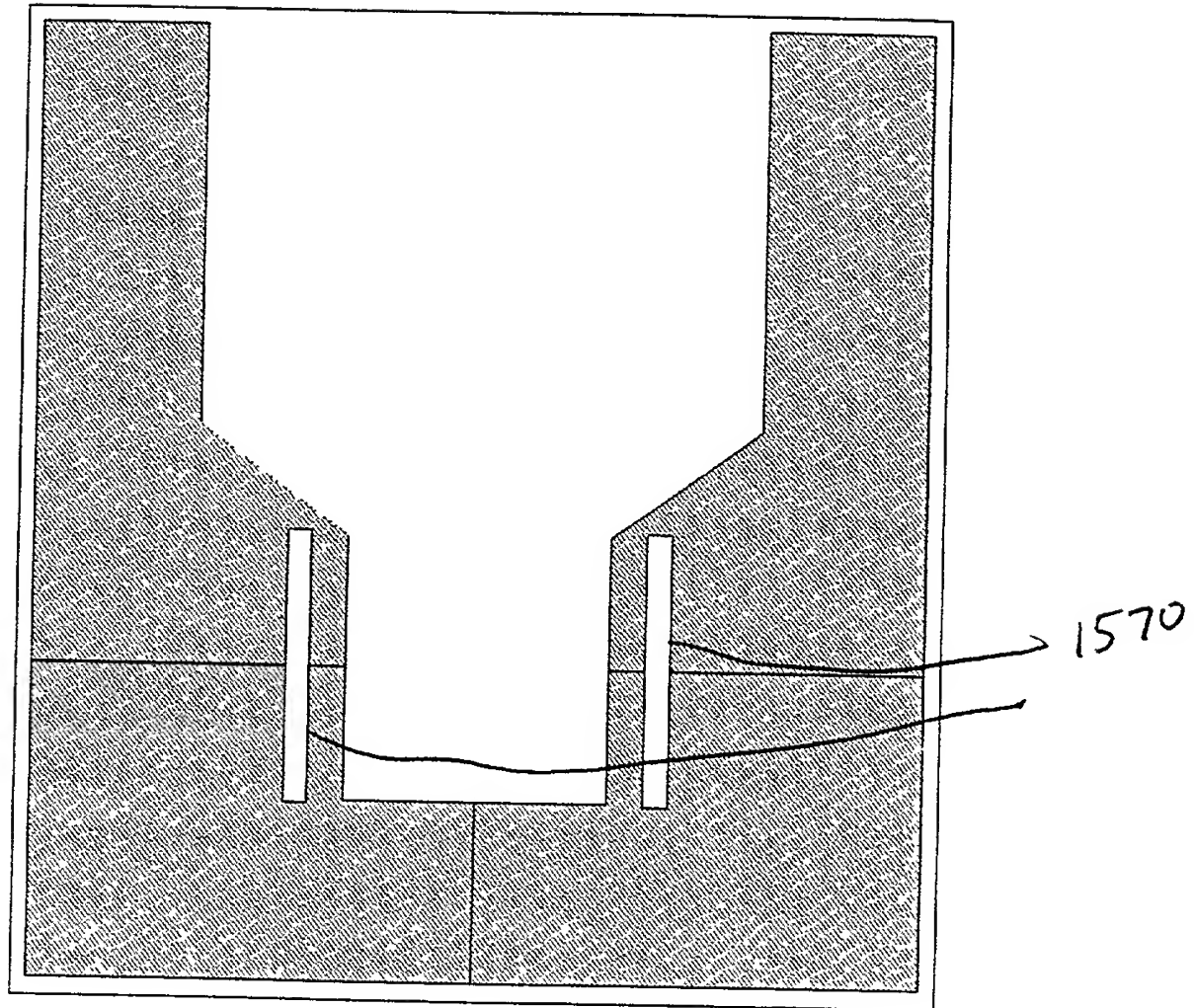


FIG. 15E

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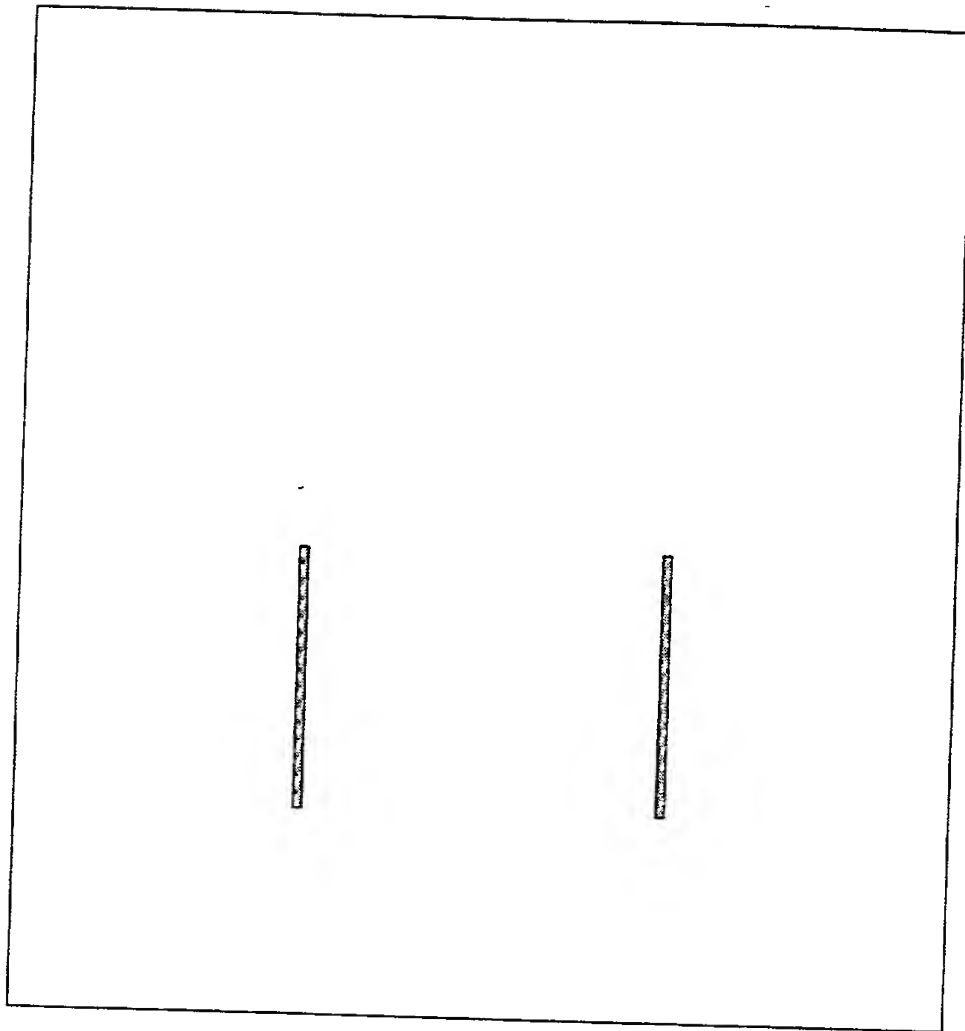


FIG. 15 F

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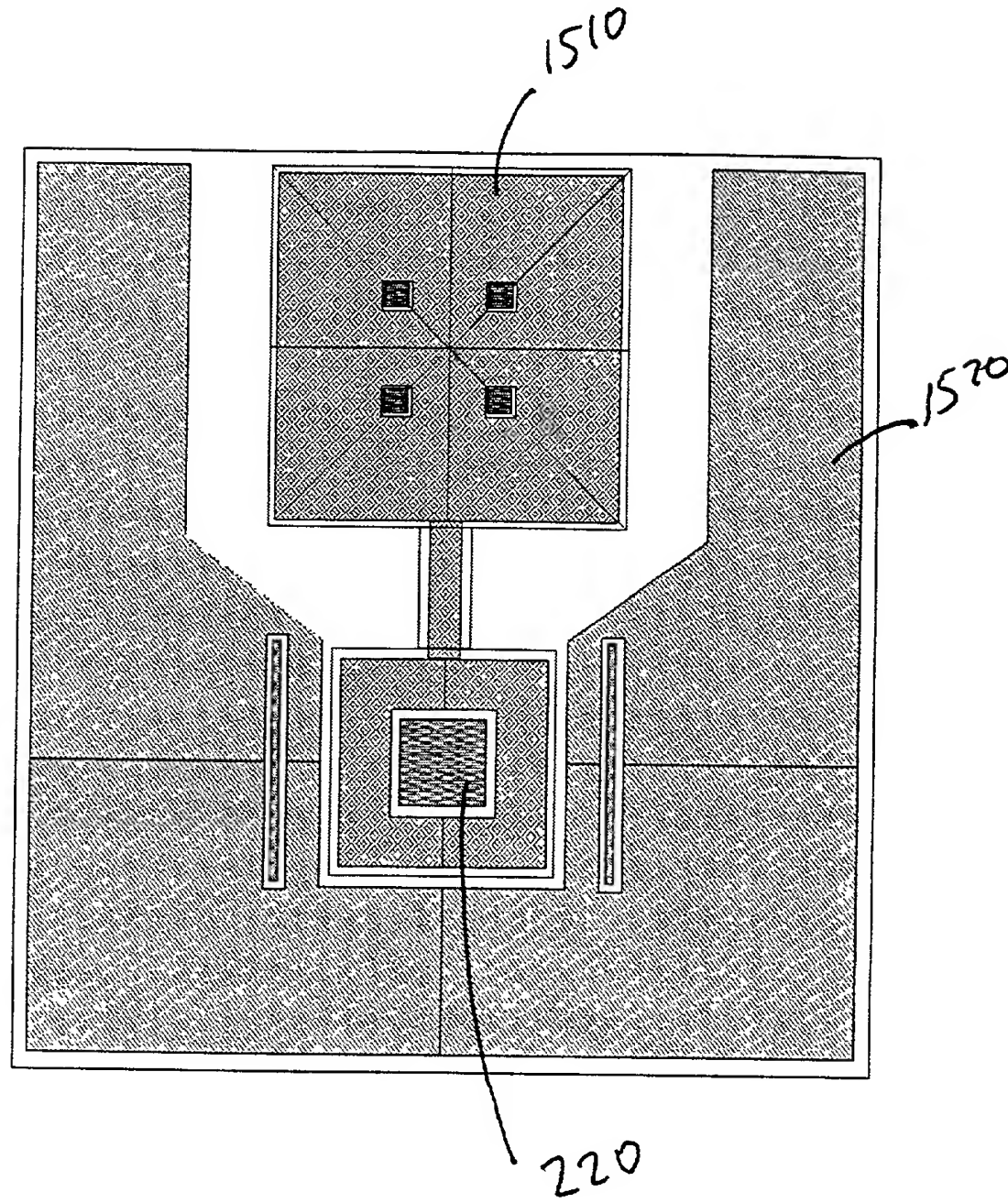


FIG. 15 G

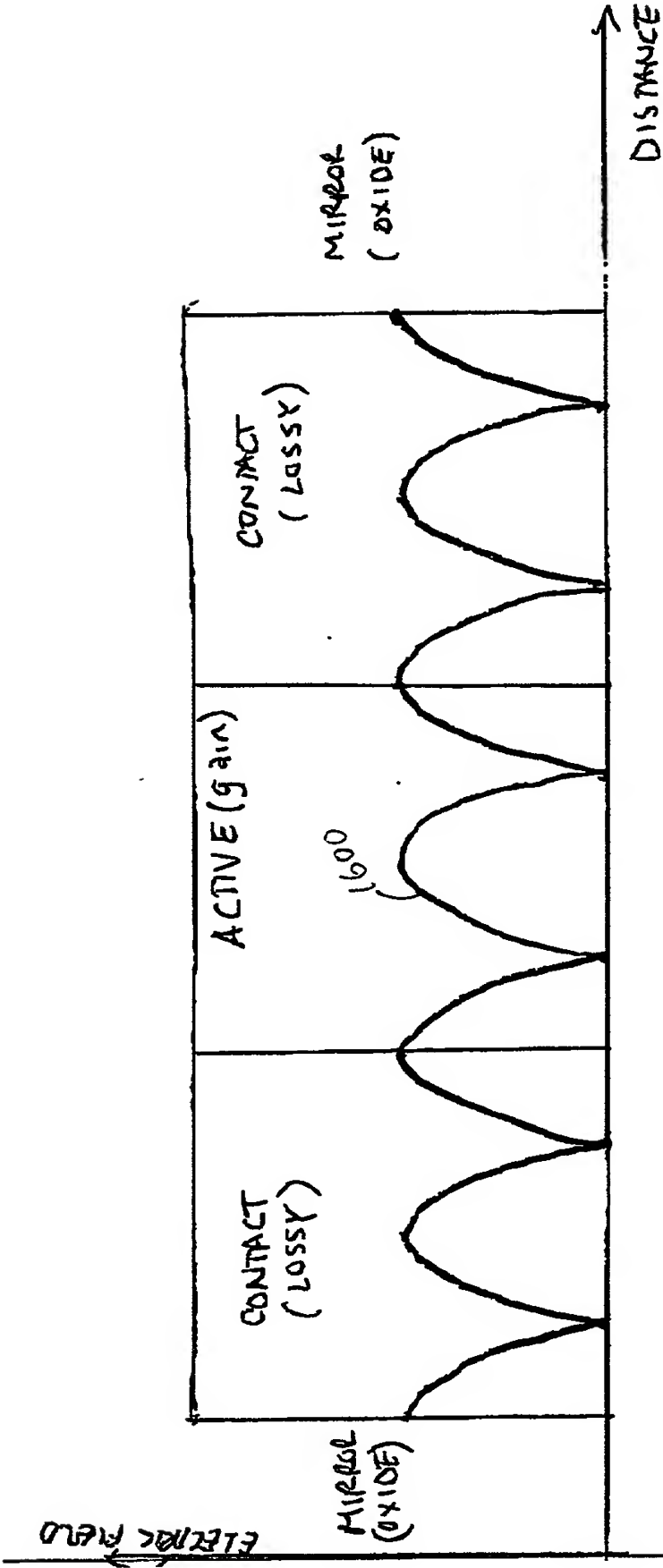


FIG. 16A



FT 6. 16 B